

PATENT APPLICATION *Ec 6/2000*  
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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Makoto KOBAYASHI et al.

Group Art Unit: 3723

Application No.: 09/830,434

Examiner: H. Shakeri

Filed: April 26, 2001

Docket No.: 109352

For: POLISHING PAD AND POLISHING METHOD FOR SEMICONDUCTOR WAFER

AMENDMENTDirector of the U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed November 7, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 19 without prejudice to or disclaimer of the subject matter contained therein.

Please replace claims 15, 17, 18, 20-29 and 31 as follows:

*B1*  
15. (Amended) The polishing pad used for polishing a semiconductor wafer according to Claim 12, which comprises a base layer formed of nonwoven fabric and a porous surface layer.

*B2*  
17. (Amended) The polishing pad used for polishing a semiconductor wafer according to Claim 14, wherein a content of zinc compounds in the porous surface layer is 100ppm or less at the ratio of zinc weight relative to the weight of the porous surface layer.